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Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PB[7]	PCR[23]	AF0 AF1 AF2 AF3 —	GPIO[23] — — — ADC1_P[3]	SIUL — — — ADC	I — — — I	I	Tristate	37	55
PB[8]	PCR[24]	AF0 AF1 AF2 AF3 — —	GPIO[24] — — — ADC1_S[4] WKPU[25][3]	SIUL — — — ADC WKPU	I — — — I I	I	Tristate	30	39
PB[9]	PCR[25]	AF0 AF1 AF2 AF3 — —	GPIO[25] — — — ADC1_S[5] WKPU[26][3]	SIUL — — — ADC WKPU	I — — — I I	I	Tristate	29	38
PB[10]	PCR[26]	AF0 AF1 AF2 AF3 — —	GPIO[26] — — — ADC1_S[6] WKPU[8][3]	SIUL — — — ADC WKPU	I/O — — — I I	J	Tristate	31	40
PB[11]	PCR[27]	AF0 AF1 AF2 AF3 —	GPIO[27] E0UC[3] — CS0_0 ADC1_S[12]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — I/O I	J	Tristate	38	59
PB[12]	PCR[28]	AF0 AF1 AF2 AF3 —	GPIO[28] E0UC[4] — CS1_0 ADC1_X[0]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	39	61
PB[13]	PCR[29]	AF0 AF1 AF2 AF3 —	GPIO[29] E0UC[5] — CS2_0 ADC1_X[1]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	40	63
PB[14]	PCR[30]	AF0 AF1 AF2 AF3 —	GPIO[30] E0UC[6] — CS3_0 ADC1_X[2]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	41	65

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 —	GPIO[56] — — — ADC1_P[12]	SIUL — — — ADC	I — — — I	I	Tristate	—	49
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 —	GPIO[57] — — — ADC1_P[13]	SIUL — — — ADC	I — — — I	I	Tristate	—	56
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 —	GPIO[58] — — — ADC1_P[14]	SIUL — — — ADC	I — — — I	I	Tristate	—	57
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 —	GPIO[59] — — — ADC1_P[15]	SIUL — — — ADC	I — — — I	I	Tristate	—	58
PD[12]	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ADC1_S[8]	SIUL DSPI_0 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	60
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ADC1_S[9]	SIUL DSPI_1 eMIOS_0 — ADC	I/O I/O I/O — I	J	Tristate	—	62
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 —	GPIO[62] CS1_1 E0UC[26] — ADC1_S[10]	SIUL DSPI_1 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	64
PD[15]	PCR[63]	AF0 AF1 AF2 AF3 —	GPIO[63] CS2_1 E0UC[27] — ADC1_S[11]	SIUL DSPI_1 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	66
Port E									

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PE[0]	PCR[64]	AF0 AF1 AF2 AF3 —	GPIO[64] E0UC[16] — — WKPU[6][3]	SIUL eMIOS_0 — — WKPU	I/O I/O — — I	S	Tristate	—	6
PE[1]	PCR[65]	AF0 AF1 AF2 AF3	GPIO[65] E0UC[17] — —	SIUL eMIOS_0 — —	I/O I/O — —	M	Tristate	—	8
PE[2]	PCR[66]	AF0 AF1 AF2 AF3 — —	GPIO[66] E0UC[18] — — EIRQ[21] SIN_1	SIUL eMIOS_0 — — SIUL DSPI_1	I/O I/O — — I I	M	Tristate	—	89
PE[3]	PCR[67]	AF0 AF1 AF2 AF3	GPIO[67] E0UC[19] SOUT_1 —	SIUL eMIOS_0 DSPI_1 —	I/O I/O O —	M	Tristate	—	90
PE[4]	PCR[68]	AF0 AF1 AF2 AF3 —	GPIO[68] E0UC[20] SCK_1 — EIRQ[9]	SIUL eMIOS_0 DSPI_1 — SIUL	I/O I/O I/O — I	M	Tristate	—	93
PE[5]	PCR[69]	AF0 AF1 AF2 AF3	GPIO[69] E0UC[21] CS0_1 MA[2]	SIUL eMIOS_0 DSPI_1 ADC	I/O I/O I/O O	M	Tristate	—	94
PE[6]	PCR[70]	AF0 AF1 AF2 AF3 —	GPIO[70] E0UC[22] CS3_0 MA[1] EIRQ[22]	SIUL eMIOS_0 DSPI_0 ADC SIUL	I/O I/O O O I	M	Tristate	—	95
PE[7]	PCR[71]	AF0 AF1 AF2 AF3 —	GPIO[71] E0UC[23] CS2_0 MA[0] EIRQ[23]	SIUL eMIOS_0 DSPI_0 ADC SIUL	I/O I/O O O I	M	Tristate	—	96
PE[8]	PCR[72]	AF0 AF1 AF2 AF3	GPIO[72] — E0UC[22] —	SIUL — eMIOS_0 —	I/O — I/O —	M	Tristate	—	9

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PE[9]	PCR[73]	AF0 AF1 AF2 AF3 —	GPIO[73] — E0UC[23] — WKPU[7][3]	SIUL — eMIOS_0 — WKPU	I/O — I/O — I	S	Tristate	—	10
PE[10]	PCR[74]	AF0 AF1 AF2 AF3 —	GPIO[74] — CS3_1 — EIRQ[10]	SIUL — DSPI_1 — SIUL	I/O — O — I	S	Tristate	—	11
PE[11]	PCR[75]	AF0 AF1 AF2 AF3 —	GPIO[75] E0UC[24] CS4_1 — WKPU[14][3]	SIUL eMIOS_0 DSPI_1 — WKPU	I/O I/O O — I	S	Tristate	—	13
PE[12]	PCR[76]	AF0 AF1 AF2 AF3 — —	GPIO[76] — — — ADC1_S[7] EIRQ[11]	SIUL — — — ADC SIUL	I/O — — — I I	S	Tristate	—	76
Port H									
PH[9][6]	PCR[121]	AF0 AF1 AF2 AF3	GPIO[121] — TCK —	SIUL — JTAGC —	I/O — I —	S	Input, weak pull-up	60	88
PH[10][6]	PCR[122]	AF0 AF1 AF2 AF3	GPIO[122] — TMS —	SIUL — JTAGC —	I/O — I —	S	Input, weak pull-up	53	81

1 Alternate functions are chosen by setting the values of the PCR.PA bitfields inside the SIUL module. PCR.PA = 00 → AF0; PCR.PA = 01 → AF1; PCR.PA = 10 → AF2; PCR.PA = 11 → AF3. This is intended to select the output functions; to use one of the input functions, the PCR.IBE bit must be written to '1', regardless of the values selected in the PCR.PA bitfields. For this reason, the value corresponding to an input only function is reported as "—".

2 Multiple inputs are routed to all respective modules internally. The input of some modules must be configured by setting the values of the PSMIO.PADSELx bitfields inside the SIUL module.

3 All WKPU pins also support external interrupt capability. See "wakeup unit" chapter of the device reference manual for further details.

4 NMI has higher priority than alternate function. When NMI is selected, the PCR.AF field is ignored.

5 "Not applicable" because these functions are available only while the device is booting. Refer to "BAM" chapter of the device reference manual for details.

4.7.4 Output pin transition times

Table 18. Output pin transition times

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
t_{tr}	CC	D	Output transition time output pin[2] SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	50	ns
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
t_{tr}	CC	D	Output transition time output pin(2) MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 SIUL.PCRx.SRC = 1	—	—	10	ns
		T		C_L = 50 pF		—	—	20	
		D		C_L = 100 pF		—	—	40	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 SIUL.PCRx.SRC = 1	—	—	12	
		T		C_L = 50 pF		—	—	25	
		D		C_L = 100 pF		—	—	40	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 C_L includes device and package capacitances (C_{PKG} < 5 pF).

4.7.5 I/O pad current specification

The I/O pads are distributed across the I/O supply segment. Each I/O supply segment is associated to a V_{DD}/V_{SS} supply pair as described in Table 19.

Table 20 provides I/O consumption figures.

In order to ensure device reliability, the average current of the I/O on a single segment should remain below the I_{AVGSEG} maximum value.

Table 19. I/O supply segment

Package	Supply segment			
	1	2	3	4
100 LQFP	pin 16 – pin 35	pin 37 – pin 69	pin 70 – pin 83	pin 84 – pin 15
64 LQFP	pin 8 – pin 26	pin 28 – pin 55	pin 56 – pin 7	—

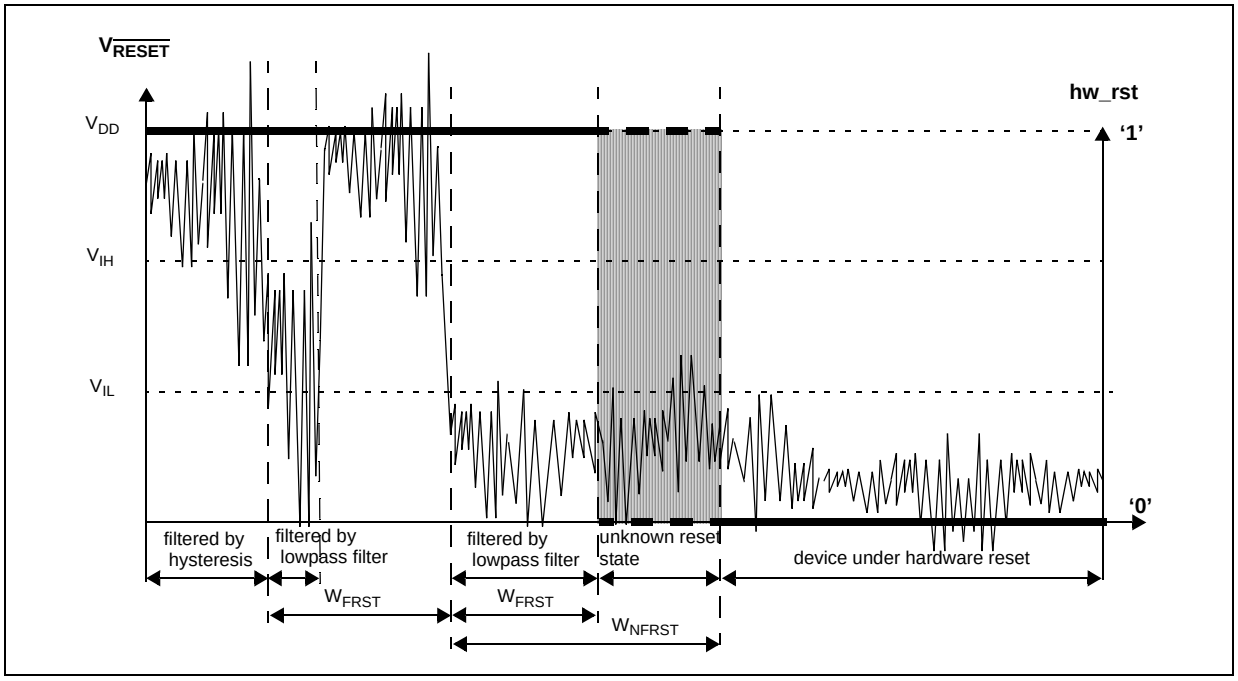

Figure 6. Noise filtering on reset signal

Table 22. Reset electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	V_{DD} + 0.4	V
V_{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	—	–0.4	—	$0.35V_{DD}$	V
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	$0.1V_{DD}$	—	—	V
V_{OL}	CC	P	Output low level	Push Pull, I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
				Push Pull, I_{OL} = 1 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	—	—	$0.1V_{DD}$	
				Push Pull, I_{OL} = 1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	

— LV_CFLA: Low voltage supply for code flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
— LV_DFLA: Low voltage supply for data flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
— LV_PLL: Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.

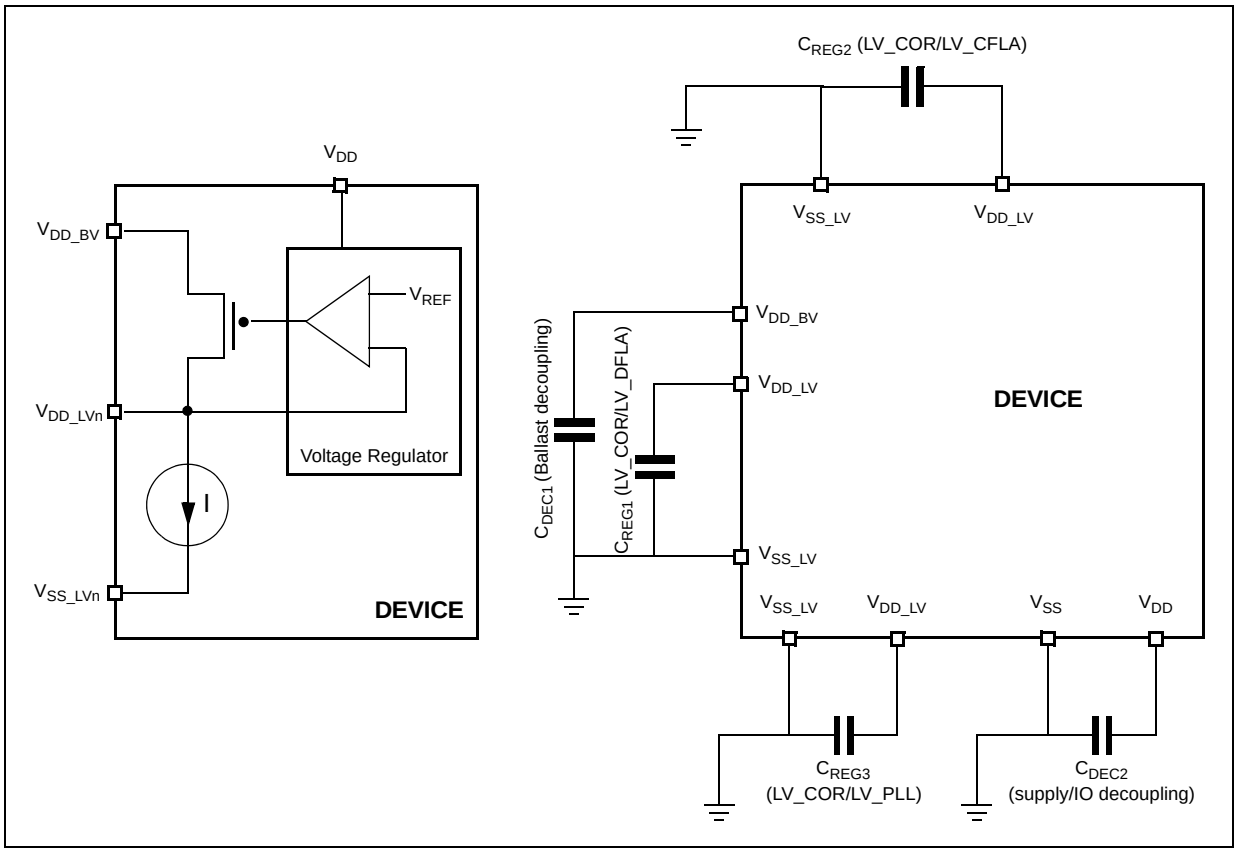

Figure 7. Voltage regulator capacitance connection

The internal voltage regulator requires external capacitance (C_{REGn}) to be connected to the device in order to provide a stable low voltage digital supply to the device. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the board to less than 5 nH.

Each decoupling capacitor must be placed between each of the three V_{DD_LV}/V_{SS_LV} supply pairs to ensure stable voltage (see Section 4.5, Recommended operating conditions).

Table 23. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
C_{REGn}	SR	—	Internal voltage regulator external capacitance	—	200	—	500	nF
R_{REG}	SR	—	Stability capacitor equivalent serial resistance	Range: 10 kHz to 20 MHz	—	—	0.2	Ω

4.9.2 Low voltage detector electrical characteristics

The device implements a power-on reset (POR) module to ensure correct power-up initialization, as well as five low voltage detectors (LVDs) to monitor the V_{DD} and the V_{DD_LV} voltage while device is supplied:

- POR monitors V_{DD} during the power-up phase to ensure device is maintained in a safe reset state (refer to RGM Destructive Event Status (RGM_DES) Register flag F_POR in device reference manual)
- LVDHV3 monitors V_{DD} to ensure device reset below minimum functional supply (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD27 in device reference manual)
- LVDHV3B monitors V_{DD_BV} to ensure device reset below minimum functional supply (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD27_VREG in device reference manual)
- LVDHV5 monitors V_{DD} when application uses device in the 5.0 V ± 10% range (refer to RGM Functional Event Status (RGM_FES) Register flag F_LVD45 in device reference manual)
- LVDLVCOR monitors power domain No. 1 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD1 in device reference manual)
- LVDLVBKP monitors power domain No. 0 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD0 in device reference manual)

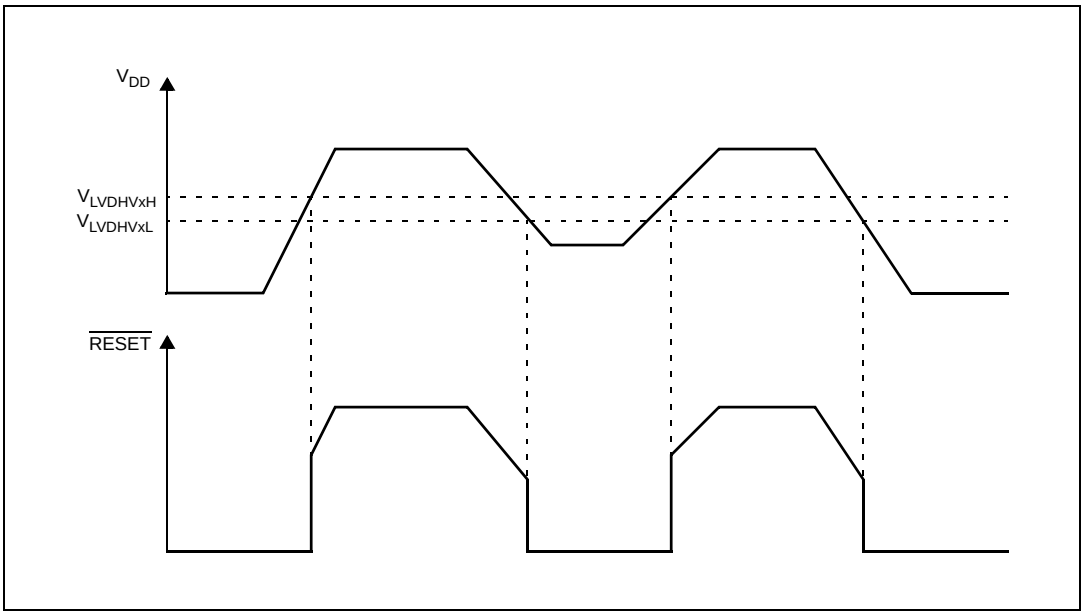

Figure 8. Low voltage detector vs reset

Table 30. Flash power supply DC electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{FLPW}	CC	D	Sum of the current consumption on V_{DDHV} and V_{DDBV} during flash low-power mode	—	Code flash	—	—	910	µA
I_{CFPWD}	CC	D	Sum of the current consumption on V_{DDHV} and V_{DDBV} during flash power-down mode	—	Code flash	—	—	125	µA
I_{DFPWD}	CC	D			Data flash	—	—	25	µA

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

4.11.3 Start-up/Switch-off timings

Table 31. Start-up time/Switch-off time

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
$t_{FLARSTEXIT}$	CC	T	Delay for flash module to exit reset mode	Code flash	—	—	125	µs
				Data flash	—	—	150	µs
$t_{FLALPEXIT}$	CC	T	Delay for flash module to exit low-power mode[2]	Code flash	—	—	0.5	µs
$t_{FLAPDEXIT}$	CC	T	Delay for flash module to exit power-down mode	Code flash	—	—	30	µs
				Data flash	—	—	30[3]	µs
$t_{FLALPENTRY}$	CC	T	Delay for flash module to enter low-power mode	Code flash	—	—	0.5	µs
$t_{FLAPDENTRY}$	CC	T	Delay for flash module to enter power-down mode	Code flash	—	—	1.5	µs
				Data flash	—	—	4(3)	µs

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 Data flash does not support low-power mode

3 If code flash is already switched-on.

4.12 Electromagnetic compatibility (EMC) characteristics

Susceptibility tests are performed on a sample basis during product characterization.

4.12.1 Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user apply EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

- Software recommendations – The software flowchart must include the management of runaway conditions such as:

Table 38. Fast internal RC oscillator (16 MHz) electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
$I_{FIRCSTOP}$	CC	T	Fast internal RC oscillator high frequency and system clock current in stop mode	T_A = 25 °C	sysclk = off	—	500	—	µA
					sysclk = 2 MHz	—	600	—	
					sysclk = 4 MHz	—	700	—	
					sysclk = 8 MHz	—	900	—	
					sysclk = 16 MHz	—	1250	—	
t_{FIRCSU}	CC	C	Fast internal RC oscillator start-up time	V_{DD} = 5.0 V ± 10%		—	1.1	2.0	µs
$\Delta_{FIRCPRE}$	CC	C	Fast internal RC oscillator precision after software trimming of f_{FIRC}	T_A = 25 °C		–1	—	1	%
$\Delta_{FIRCTRIM}$	CC	C	Fast internal RC oscillator trimming step	T_A = 25 °C		—	1.6		%
$\Delta_{FIRCVAR}$	CC	C	Fast internal RC oscillator variation in temperature and supply with respect to f_{FIRC} at T_A = 55 °C in high-frequency configuration	—		–5	—	5	%

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 This does not include consumption linked to clock tree toggling and peripherals consumption when RC oscillator is ON.

4.16 Slow internal RC oscillator (128 kHz) electrical characteristics

The device provides a 128 kHz slow internal RC oscillator (SIRC). This can be used as the reference clock for the RTC module.

Table 39. Slow internal RC oscillator (128 kHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
f_{SIRC}	CC	P	Slow internal RC oscillator low frequency	T_A = 25 °C, trimmed	—	128	—	kHz
	SR	—		—	100	—	150	
I_{SIRC}[2],	CC	C	Slow internal RC oscillator low frequency current	T_A = 25 °C, trimmed	—	—	5	µA
t_{SIRCSU}	CC	P	Slow internal RC oscillator start-up time	T_A = 25 °C, V_{DD} = 5.0 V ± 10%	—	8	12	µs
$\Delta_{SIRCPRE}$	CC	C	Slow internal RC oscillator precision after software trimming of f_{SIRC}	T_A = 25 °C	–2	—	2	%
$\Delta_{SIRCTRIM}$	CC	C	Slow internal RC oscillator trimming step	—	—	2.7	—	

4.17.2 Input impedance and ADC accuracy

In the following analysis, the input circuit corresponding to the precise channels is considered.

To preserve the accuracy of the A/D converter, it is necessary that analog input pins have low AC impedance. Placing a capacitor with good high frequency characteristics at the input pin of the device can be effective: the capacitor should be as large as possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: being C_S and C_{p2} substantially two switched capacitances, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S+C_{p2} equal to 3 pF, a resistance of 330 kΩ is obtained ($R_{EQ} = 1 / (f_c \times (C_S+C_{p2}))$, where f_c represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S+C_{p2}) and the sum of $R_S + R_F$, the external circuit must be designed to respect the Equation 4:

Eqn. 4

$$V_A \bullet \frac{R_S + R_F}{R_{EQ}} < \frac{1}{2} \mathrm{LSB}$$

Equation 4 generates a constraint for external network design, in particular on a resistive path.

In particular two different transient periods can be distinguished:

1. A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Eqn. 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time t_s is always much longer than the internal time constant:

Eqn. 6

$$\tau_1 < (R_{SW} + R_{AD}) \bullet C_S \ll t_s$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S, determining a new value of the voltage V_{A1} on the capacitance according to Equation 7:

Eqn. 7

$$V_{A1} \bullet (C_S + C_{P1} + C_{P2}) = V_A \bullet (C_{P1} + C_{P2})$$

2. A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Eqn. 8

$$\tau_2 < R_L \bullet (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time t_s, a constraints on R_L sizing is obtained:

Eqn. 9

$$10 \bullet \tau_2 = 10 \bullet R_L \bullet (C_S + C_{P1} + C_{P2}) < t_s$$

Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1}, C_{P2} and C_S, then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1}. Equation 10 must be respected (charge balance assuming now C_S already charged at V_{A1}):

Eqn. 10

$$V_{A2} \bullet (C_S + C_{P1} + C_{P2} + C_F) = V_A \bullet C_F + V_{A1} \bullet (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the $R_F C_F$ filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A; the time constant $R_F C_F$ of the filter is very high with respect to the sampling time (t_s). The filter is typically designed to act as anti-aliasing.

Table 41. ADC conversion characteristics (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
t_c	CC	P	Conversion time[6] V_{DD} = 3.3 V	f_{ADC} = 20 MHz, INPCMP = 0		2.4	—	—	µs
				f_{ADC} = 13.33 MHz, INPCMP = 0		—	—	3.6	
		P	Conversion time[(6)] V_{DD} = 5.0 V	f_{ADC} = 32 MHz, INPCMP = 0		1.5	—	—	µs
				f_{ADC} = 13.33 MHz, INPCMP = 0		—	—	3.6	
C_S	CC	D	ADC input sampling capacitance	—		5			pF
C_{P1}	CC	D	ADC input pin capacitance 1	—		3			pF
C_{P2}	CC	D	ADC input pin capacitance 2	—		1			pF
C_{P3}	CC	D	ADC input pin capacitance 3	—		1.5			pF
R_{SW1}	CC	D	Internal resistance of analog source	—		—	—	1	kΩ
R_{SW2}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
R_{AD}	CC	D	Internal resistance of analog source	—		—	—	0.3	kΩ
I_{INJ}	SR	—	Input current Injection	Current injection on one ADC input, different from the converted one	V_{DD} = 3.3 V ± 10%	–5	—	5	mA
					V_{DD} = 5.0 V ± 10%	–5	—	5	
INLP	CC	T	Absolute Integral non-linearity-precise channels	No overload		—	1	3	LSB
INLX	CC	T	Absolute Integral non-linearity-extended channels	No overload		—	1.5	5	LSB
DNL	CC	T	Absolute Differential non-linearity	No overload		—	0.5	1	LSB
E_O	CC	T	Absolute Offset error	—		—	2	—	LSB
E_G	CC	T	Absolute Gain error	—		—	2	—	LSB
TUEP[7]	CC	P	Total unadjusted error for precise channels, input only pins	Without current injection		–6		6	LSB
		T		With current injection		–8		8	

Table 41. ADC conversion characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
TUEX[7]	CC	T	Total unadjusted error for extended channel	Without current injection	–10		10	LSB
		T		With current injection	–12		12	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 Analog and digital V_{SS} **must** be common (to be tied together externally).

3 V_{AINx} may exceed V_{SS_ADC} and V_{DD_ADC} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0xFFF.

4 Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

5 During the sampling time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_S. After the end of the sampling time t_S, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_S depend on programming.

6 This parameter does not include the sampling time t_S, but only the time for determining the digital result and the time to load the result's register with the conversion result.

7 Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

4.18 On-chip peripherals

4.18.1 Current consumption

Table 42. On-chip peripherals current consumption[1]

Symbol		C	Parameter	Conditions		Typical value[2]	Unit
$I_{DD\_BV(CAN)}$	CC	T	CAN (FlexCAN) supply current on V_{DD_BV}	500 Kbyte/s	Total (static + dynamic) consumption: • FlexCAN in loop-back mode • XTAL at 8 MHz used as CAN engine clock source • Message sending period is 580 µs	8 × f_{periph} + 85	µA
				125 Kbyte/s		8 × f_{periph} + 27	µA
$I_{DD\_BV(eMIOS)}$	CC	T	eMIOS supply current on V_{DD_BV}	Static consumption: • eMIOS channel OFF • Global prescaler enabled		29 × f_{periph}	µA
				Dynamic consumption: • It does not change varying the frequency (0.003 mA)		3	µA
$I_{DD\_BV(SCI)}$	CC	T	SCI (LINFlex) supply current on V_{DD_BV}	Total (static + dynamic) consumption: • LIN mode • Baudrate: 20 Kbyte/s		5 × f_{periph} + 31	µA

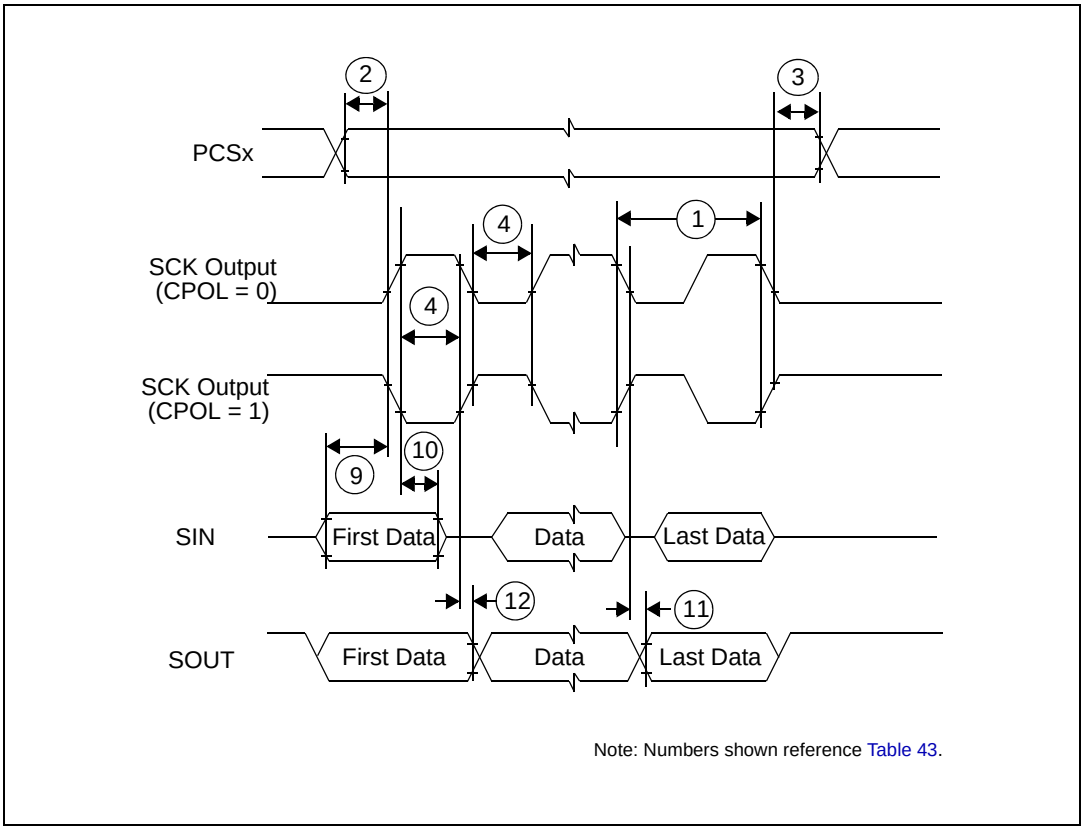

Figure 16. DSPI classic SPI timing – master, CPHA = 0

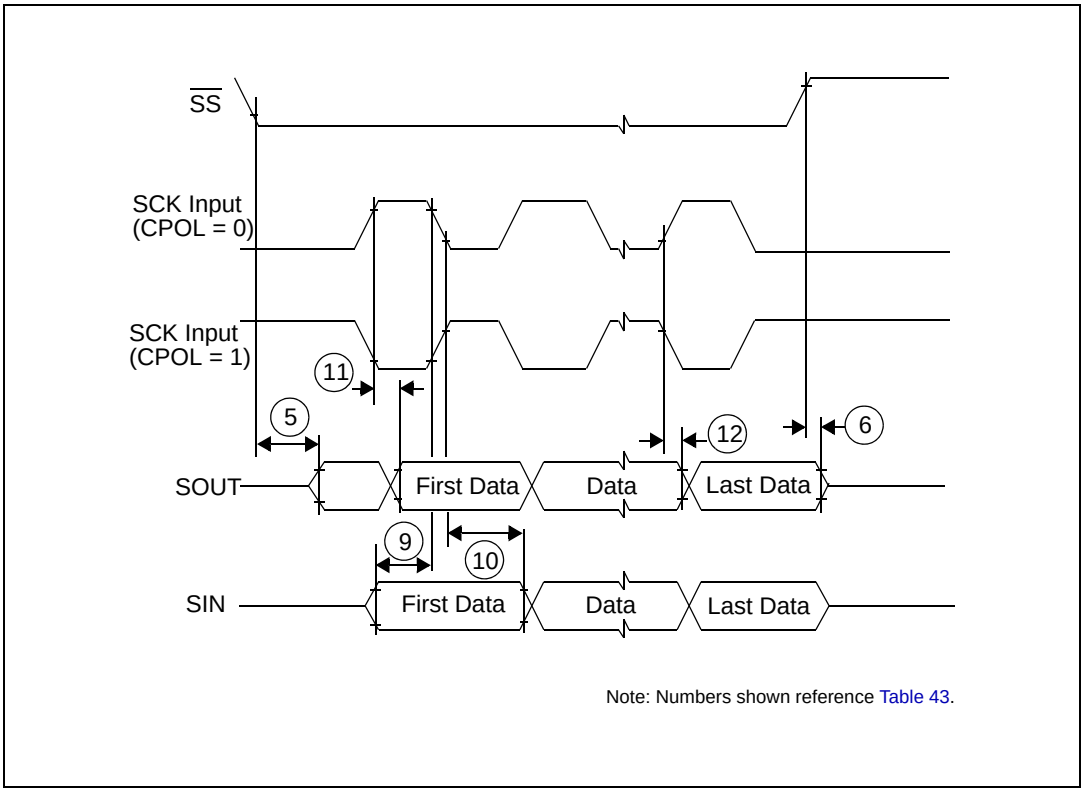

Figure 23. DSPI modified transfer format timing – slave, CPHA = 1

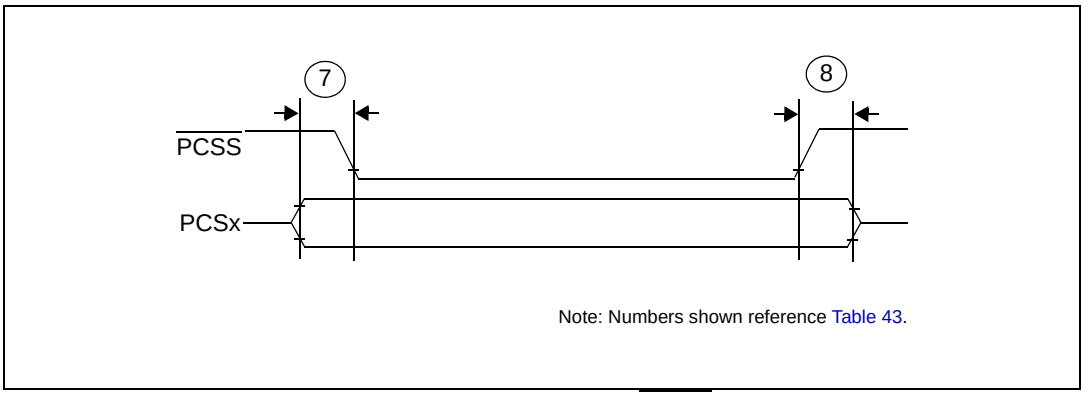

Figure 24. DSPI PCS strobe (PCSS) timing

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		PAGE: 983
	DO NOT SCALE THIS DRAWING	REV: H

NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.

3. DATUMS B, C AND D TO BE DETERMINED AT DATUM PLANE H.

4. THE TOP PACKAGE BODY SIZE MAY BE SMALLER THAN THE BOTTOM PACKAGE SIZE BY A MAXIMUM OF 0.1 MM.

5. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSIONS. THE MAXIMUM ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THE DIMENSIONS ARE MAXIMUM BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.

6. DIMENSION DOES NOT INCLUDE DAM BAR PROTRUSION. PROTRUSIONS SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.35. MINIMUM SPACE BETWEEN PROTRUSION AND AN ADJACENT LEAD SHALL BE 0.07 MM.

7. DIMENSIONS ARE DETERMINED AT THE SEATING PLANE, DATUM A.

TITLE: 100 LEAD LQFP 14 X 14, 0.5 PITCH, 1.4 THICK	CASE NUMBER: 983–02	
	STANDARD: NON–JEDEC	
	PACKAGE CODE: 8264	SHEET: 3

Figure 28. 100 LQFP package mechanical drawing (Part 3 of 3)

7 Document revision history

Table 45 summarizes revisions to this document.

Table 45. Revision history

Revision	Date	Description of Changes
1	30 Sep 2009	Initial release
2	18 Feb 2010	Updated the following tables: - Absolute maximum ratings - Low voltage power domain electrical characteristics; - On-chip peripherals current consumption - DSPI characteristics; - JTAG characteristics; - ADC conversion characteristics; Inserted a note on “Flash power supply DC characteristics” section.
3	10 Aug 2010	“Features” section: Updated information concerning eMIOS, ADC, LINFlex, Nexus and low power capabilities “MPC5602D device comparison” table: updated the “Execution speed” row “MPC5602D series block diagram” figure: • updated max number of Crossbar Switches • updated Legend “MPC5602D series block summary” table: added contents concernig the eDMA block “100 LQFP pin configuration (top view)” figure: • removed alternate functions • updated supply pins “64 LQFP pin configuration (top view)” figure: removed alternate functions Added “Pin muxing” section “NVUSRO register” section: Deleted “NVUSRO[WATCHDOG_EN] field description“ section “Recommended operating conditions (3.3 V)” table: • TV_{DD}: deleted min value • In footnote No. 3, changed capacitance value between V_{DD_BV} and V_{SS_LV} “Recommended operating conditions (5.0 V)” table: deleted TV_{DD} min value “LQFP thermal characteristics” table: changed $R_{\theta JC}$ values “I/O input DC electrical characteristics” table: • W_{FI}: updated max value • W_{NFI}: updated min value “I/O consumption” table: removed I_{DYNSEG} row Added “I/O weight” table “Program and erase specifications (Code Flash)” table: deleted T_{Bank_C} row Updated the following tables: • “Voltage regulator electrical characteristics” • “Low voltage monitor electrical characteristics” • “Low voltage power domain electrical characteristics” • “Start-up time/Switch-off time” • “Fast external crystal oscillator (4 to 16 MHz) electrical characteristics” • “FMPLL electrical characteristics” • “Fast internal RC oscillator (16 MHz) electrical characteristics” • “ADC conversion characteristics” • “On-chip peripherals current consumption” • “DSPI characteristics” “DSPI characteristics” section: removed “DSPI PCS strobe (PCSS) timing” figure
3 (continued)	10 Aug 2010	“Ordering information” section: removed “Orderable part number summary“ table

Table 45. Revision history (continued)

Revision	Date	Description of Changes
5	—	Rev. 5 not published.
6	29 Jan 2013	Removed all instances of table footnote “All values need to be confirmed during device validation” Section 4.1, “Introduction, removed Caution note. In Table 42, On-chip peripherals current consumption, replaced “TBD” with “8.21 mA” in $I_{DD\_HV(FLASH)}$ cell. Updated Section 4.17.2, “Input impedance and ADC accuracy In Table 24, changed $V_{LVDHV3L}$, $V_{LVDHV3BL}$ from 2.7 V to 2.6 V. Revised the Table 28 (Flash module life) Updated Table 43, DSPI characteristics, to add specifications 7 and 8, t_{PCSC} and t_{PASC}. Inserted Figure 24, DSPI PCS strobe (PCSS) timing.

Appendix A Abbreviations

Table A-1 lists abbreviations used in this document.

Table A-1. Abbreviations

Abbreviation	Meaning
APU	Auxilliary processing unit
CMOS	Complementary metal–oxide–semiconductor
CPHA	Clock phase
CPOL	Clock polarity
CS	Peripheral chip select
DAOC	Double action output compare
ECC	Error code correction
EVTO	Event out
GPIO	General purpose input/output
IPM	Input period measurement
IPWM	Input pulse width measurement
MB	Message buffer
MC	Modulus counter
MCB	Modulus counter buffered (up / down)
MCKO	Message clock out
MDO	Message data out
MSEO	Message start/end out
MTFE	Modified timing format enable
NVUSRO	Non-volatile user options register
OPWFMB	Output pulse width and frequency modulation buffered
OPWMB	Output pulse width modulation buffered

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